Document Number: MHL19338N

Rev. 6, 8/2006

# PCS Band RF Linear LDMOS Amplifier

Designed for ultra-linear amplifier applications in 50 ohm systems operating in the PCS frequency band. A silicon FET Class A design provides outstanding linearity and gain. In addition, the excellent group delay and phase linearity characteristics are ideal for digital modulation systems, such as TDMA and CDMA.

- Third Order Intercept: 46 dBm Typ
- Power Gain: 30 dB Typ (@ f = 1960 MHz)
- Input VSWR ≤ 1.5:1

# **Features**

- · Excellent Phase Linearity and Group Delay Characteristics
- Ideal for Feedforward Base Station Applications
- N Suffix Indicates Lead-Free Terminations

# MHL19338N

1900-2000 MHz 4.0 W, 30 dB RF LINEAR LDMOS AMPLIFIER

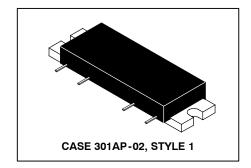


Table 1. Absolute Maximum Ratings (T<sub>C</sub> = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
DC Supply Voltage	$V_{DD}$	30	Vdc
RF Input Power	P <sub>in</sub>	+10	dBm
Storage Temperature Range	T <sub>stg</sub>	- 40 to +100	°C
Operating Case Temperature Range	T <sub>C</sub>	- 20 to +100	°C

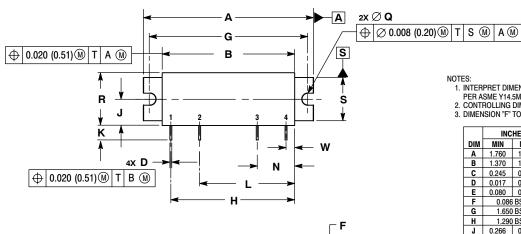
**Table 2. Electrical Characteristics** ( $V_{DD}$  = 28 Vdc,  $T_{C}$  = 25°C; 50  $\Omega$  System)

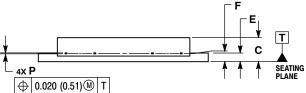
Characteristic	Symbol	Min	Тур	Max	Unit	
Supply Current		I <sub>DD</sub>	_	500	525	mA
Power Gain	(f = 1960 MHz)	G <sub>p</sub>	29	30	32	dB
Gain Flatness	(f = 1900 - 2000 MHz)	G <sub>F</sub>	_	0.1	0.4	dB
Power Output @ 1 dB Compression	(f = 1950 MHz)	P1dB	35	36	_	dBm
Third Order Intercept (f1 = 1950 MHz, f2 = 1955 MHz)		ITO	45	46	_	dBm
Noise Figure	(f = 2000 MHz)	NF	_	4.2	4.5	dB

NOTE - <u>CAUTION</u> - MOS devices are susceptible to damage from electrostatic charge. Reasonable precautions in handling and packaging MOS devices should be observed.



# **PACKAGE DIMENSIONS**





**CASE 301AP-02** ISSUE E

- NOTES:
  1. INTERPRET DIMENSIONS AND TOLERANCES
  PER ASME Y14.5M, 1994.
  2. CONTROLLING DIMENSION: INCH.
  3. DIMENSION "F" TO CENTER OF LEADS.

	INC	HES	MILLIMETERS		
DIM	MIN	MAX	MIN	MAX	
Α	1.760	1.780	44.70	45.21	
В	1.370	1.390	34.80	35.31	
C	0.245	0.265	6.22	6.73	
D	0.017	0.023	0.43	0.58	
E	0.080	0.100	2.03	2.54	
F	0.086	BSC	2.18 BSC		
G	1.650	BSC	41.91 BSC		
Н	1.290 BSC		32.77 BSC		
J	0.266	0.280	6.76	7.11	
K	0.125	0.165	3.18	4.19	
L	0.990	BSC	25.15 BSC		
N	0.390 BSC		9.91 BSC		
P	0.008	0.013	0.20	0.33	
Q	0.118	0.132	3.00	3.35	
R	0.535	0.555	13.59	14.10	
S	0.445	0.465	11.30	11.81	
W	0.090	BSC	2.29 BSC		

STYLE 1:
PIN 1. RF INPUT
2. VDD1
3. VDD2
4. RF OUTPUT
CASE: GROUND

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